

Silicon NPN Power Transistors

2SC2275 2SC2275A

DESCRIPTION

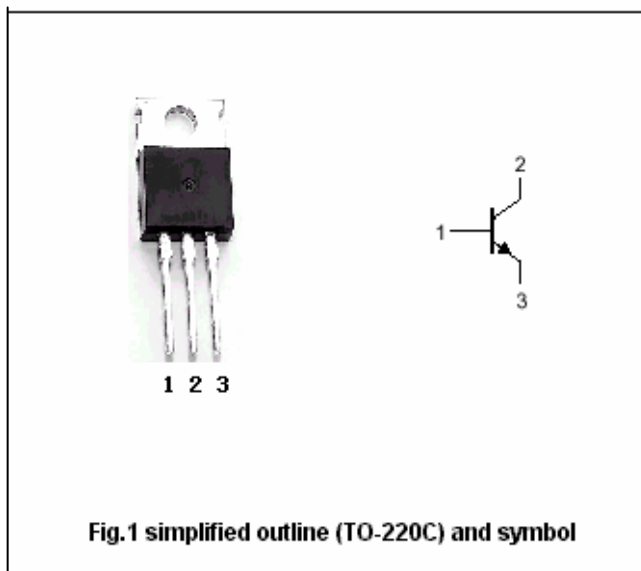
- With TO-220 package
- Complement to type 2SA985/985A
- High breakdown voltage

APPLICATIONS

- For low frequency and high frequency power amplifier applicatons

PINNING

PIN	DESCRIPTION
1	Base
2	Collector;connected to mounting base
3	Emitter

Absolute maximum ratings($T_a=25^\circ\text{C}$)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	2SC2275 Open emitter	120	V
		2SC2275A	150	
V_{CEO}	Collector-emitter voltage	2SC2275 Open base	120	V
		2SC2275A	150	
V_{EBO}	Emitter-base voltage	Open collector	5	V
I_C	Collector current		1.5	A
I_{CM}	Collector current-peak		3.0	A
I_B	Base current		0.3	A
P_C	Collector power dissipation	$T_C=25$	25	W
T_j	Junction temperature		150	
T_{stg}	Storage temperature		-55~150	

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CHARACTERISTICS

Tj=25 unless otherwise specified

SYMBOL	PARAMETER		CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	2SC2275	$I_C=25mA, I_B=0$	120			V
		2SC2275A		150			
V_{CEsat}	Collector-emitter saturation voltage		$I_C=1A; I_B=0.1A$			2.0	V
V_{BEsat}	Base-emitter saturation voltage		$I_C=1A; I_B=0.1A$			1.5	V
I_{CBO}	Collector cut-off current		$V_{CB}=120V; I_E=0$			1.0	μA
I_{EBO}	Emitter cut-off current		$V_{EB}=3V; I_C=0$			1.0	μA
h_{FE-1}	DC current gain		$I_C=5mA; V_{CE}=5V$	35			
h_{FE-2}	DC current gain		$I_C=0.3A; V_{CE}=5V$	60	150	320	
C_{OB}	Output capacitance		$I_E=0; V_{CB}=10V, f=1MHz$		19		pF
f_T	Transition frequency		$I_C=0.2A; V_{CE}=5V$		200		MHz

◆ h_{FE-2} Classifications

R	Q	P
60-120	100-200	160-320

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PACKAGE OUTLINE

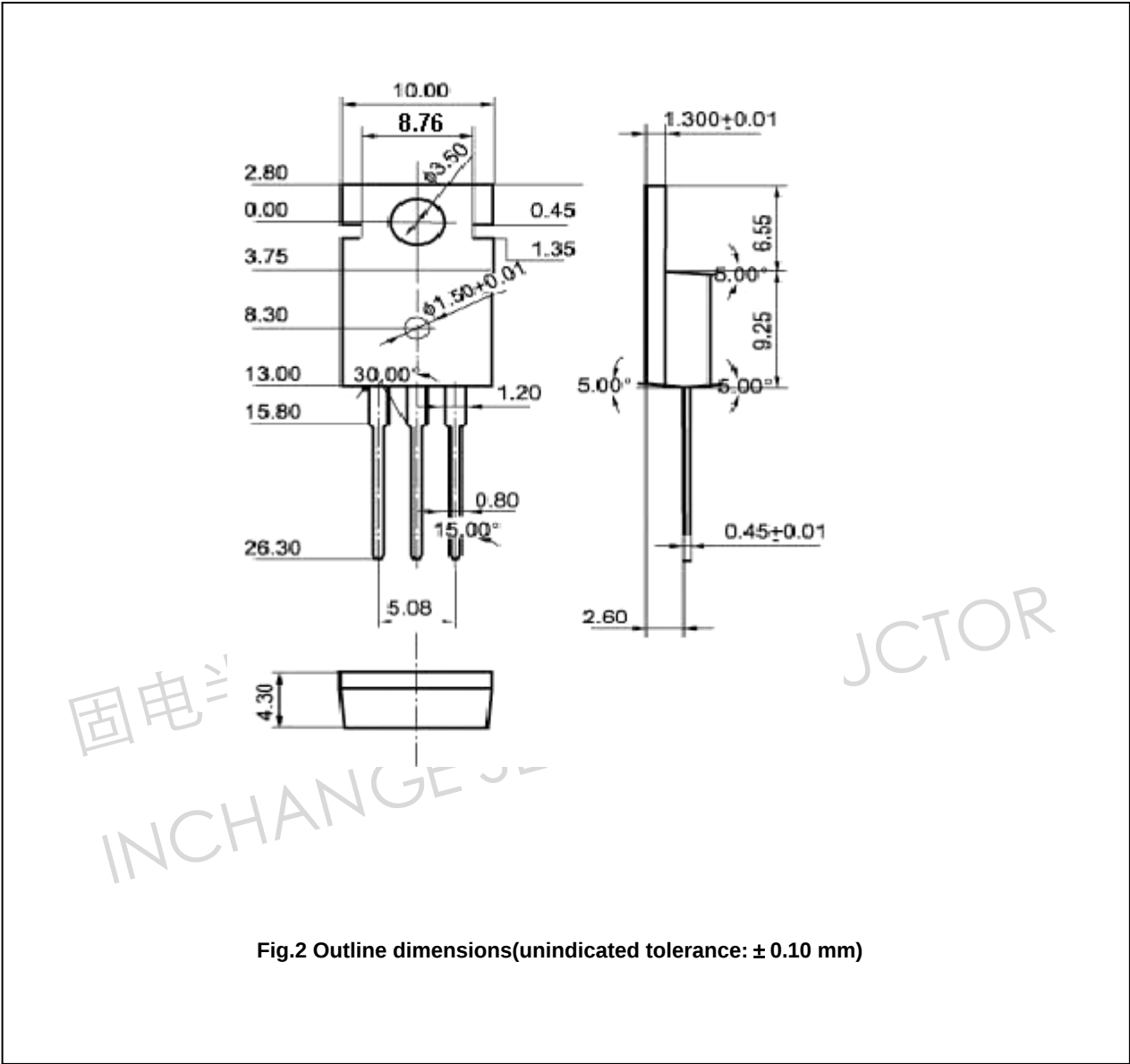


Fig.2 Outline dimensions(unindicated tolerance: ± 0.10 mm)